

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







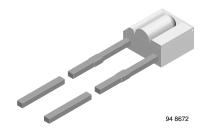
RoHS

GREEN (5-2008)**



Vishay Semiconductors

Infrared Emitting Diode, 950 nm, GaAs

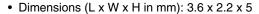


DESCRIPTION

TSSS2600 is an infrared, 950 nm emitting diode in GaAs technology, molded in a miniature, clear plastic package with side view lens.

FEATURES

Package type: leadedPackage form: side view



Peak wavelength: λ_p = 950 nm

High reliability

- · High radiant power
- · High radiant intensity
- Angle of half intensity: $\varphi = \pm 25^{\circ}$, horizontal
- · Low forward voltage
- · Suitable for high pulse current operation
- · Good spectral matching with Si photodetectors
- Package matched with detector TEST2600
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

Note

** Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

APPLICATIONS

 Infrared source in miniature light barriers or reflective sensor systems with short transmission distances and low forward voltage requirements. Matching with silicon PIN photodiodes or phototransistors (e.g. TEST2600)

PRODUCT SUMMARY					
COMPONENT	I _e (mW/sr)	φ (deg)	λ _p (nm)	tr (ns)	
TSSS2600	2.6	± 25	950	800	

Note

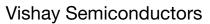
· Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TSSS2600	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	Side view	

Note

· MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current		I _F	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I _{FM}	200	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	2.0	Α	
Power dissipation		P _V	170	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 100	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T _{sd}	260	°C	
Thermal resistance junction/ambient	Leads not soldered	R _{thJA}	450	K/W	





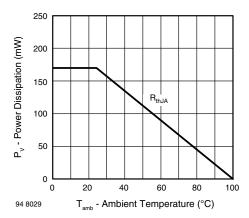


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

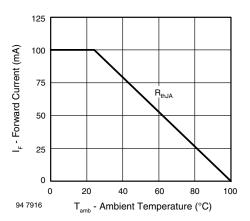


Fig. 1 - Forward Current Limit vs. Ambient Temperature

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V_{F}		1.25	1.6	V
	$I_F = 1.5 \text{ A}, t_p = 100 \mu\text{s}$	V_{F}		2.2		V
Temperature coefficient of V _F	I _F = 100 mA	TK _{VF}		- 1.3		mV/K
Reverse current	V _R = 5 V	I _R			100	μΑ
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _j		30		pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l _e	1	2.6	3	mW/sr
	$I_F = 1.5 \text{ A}, t_p = 100 \mu\text{s}$	l _e		25		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фe		20		mW
Temperature coefficient of φ _e	I _F = 100 mA	TKφ _e		- 0.8		%/K
Angle of half intensity	horizontal	Ψ1		± 25		deg
	vertical	φ ₂		± 60		deg
Peak wavelength	I _F = 100 mA	λ_{p}		950		nm
Spectral bandwidth	I _F = 100 mA	Δλ		50		nm
Temperature coefficient of λ_p	I _F = 100 mA	TKλ _p		0.2		nm/K
Rise time	I _F = 100 mA	t _r		800		ns
	I _F = 1.5 A	t _r		400		ns
E-II Kara	I _F = 100 mA	t _f		800		ns
Fall time	I _F = 1.5 A	t _f		400		ns
Virtual source diameter		d		2		mm

Vishay Semiconductors

BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

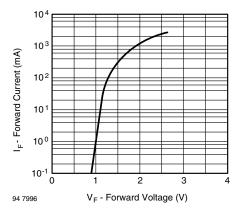


Fig. 2 - Pulse Forward Current vs. Forward Voltage

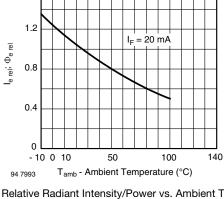


Fig. 5 - Relative Radiant Intensity/Power vs. Ambient Temperature

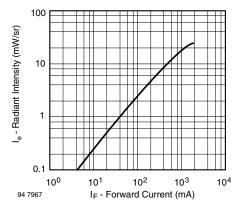


Fig. 3 - Radiant Intensity vs. Forward Current

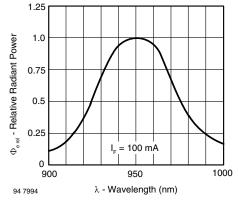


Fig. 6 - Relative Radiant Power vs. Wavelength

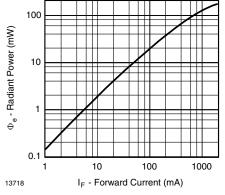


Fig. 4 - Radiant Power vs. Forward Current

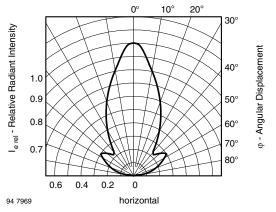


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement



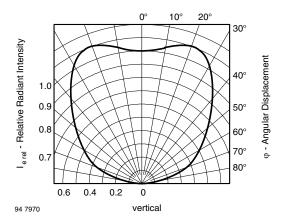
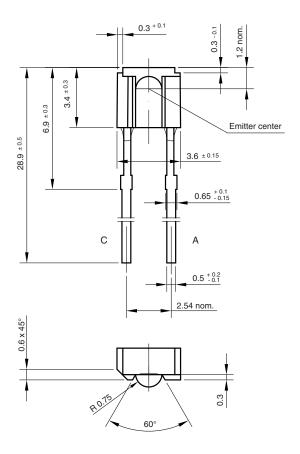


Fig. 2 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



Area not plane

1.8 ± 0.15

2.2 ± 0.15

0.4 + 0.15

technical drawings

according to DIN specifications

Drawing-No.: 6.544-5241.01-4

Issue: 3; 18.04.96

95 11488



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.